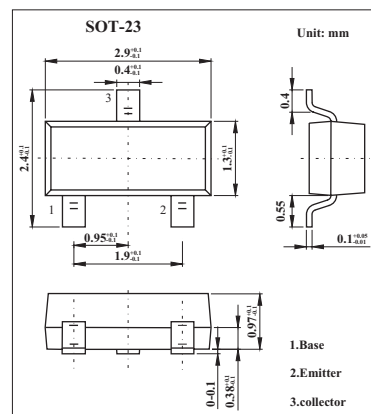


Silicon PNP Epitaxial

2SA1182

■ Features

- SOT-23 package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-35	V
Collector-emitter voltage	V_{CE0}	-30	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-500	mA
Base current	I_B	-50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{ V}, I_E = 0$			-0.1	$\mu\text{ A}$
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-0.1	$\mu\text{ A}$
DC current gain	h_{FE}	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	70		240	
		$V_{CE} = -6\text{ V}, I_C = -400\text{ mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{ mA}, I_B = -10\text{ mA}$		-0.1	-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$		-0.8	-1.0	V
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{ V}, I_E = 0, f = 1\text{ MHz}$		13		pF
Transition frequency	f_T	$V_{CE} = -6\text{ V}, I_C = -20\text{ mA}$		200		MHz

■ hFE Classification

Marking	ZO	ZY
Rank	O	Y
hFE	70~140	120~240

2SA1182

■ Typical Characteristics

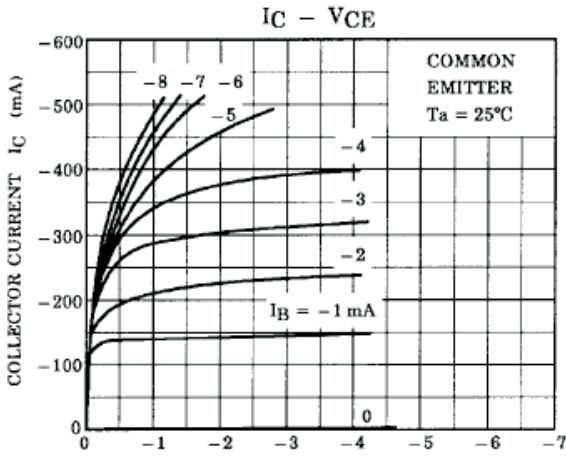


Fig. 1 Collector Emitter Voltage

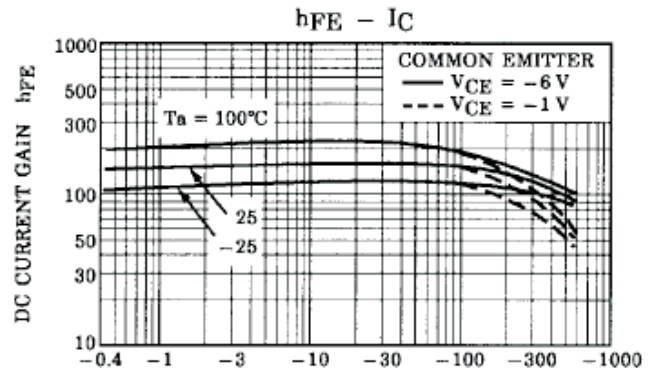


Fig.2 Collector Current

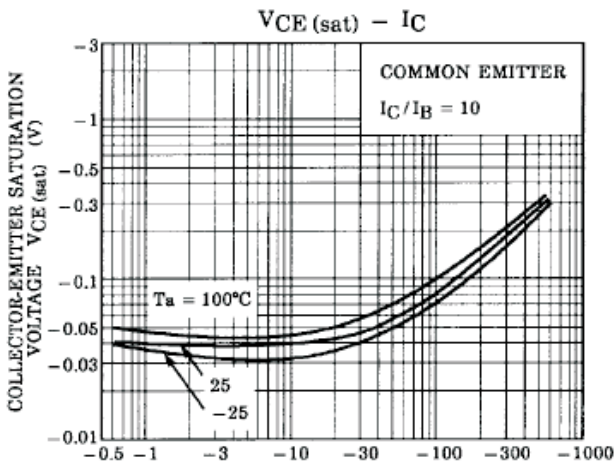


Fig.3 Collector Current

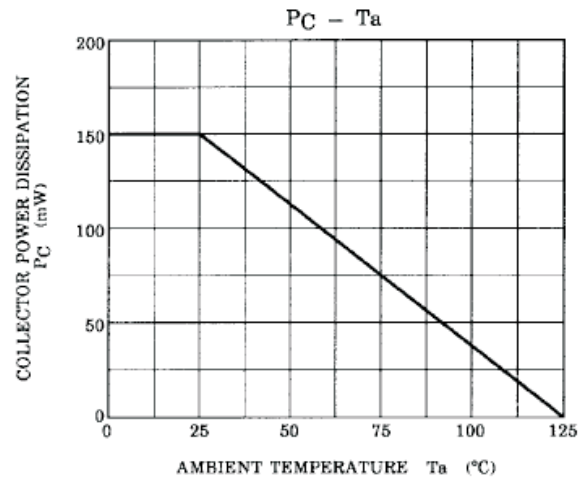


Fig.4 Ambient Temperature

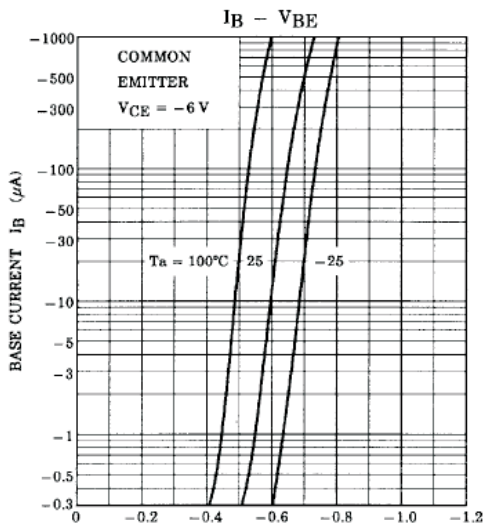


Fig.5 Base Emitter Voltage